

United Technologies Research Center

WBG Devices in Electrical Motor Drives

**NOVEL POWER SYSTEMS ENABLED BY WIDE BAND-GAP
SEMICONDUCTORS WORKSHOP**

Vladimir Blasko, UTRC

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Figure of Merits, Grand Challenge and Gaps

Performance Indices

Have different weights for different applications, two examples below:

(A) Aerospace and high end drives:

- Power per weight [kW/kg], 10 kW/kg
- Power density [kW/dm³], 10 kW/dm³
- Relative cost [kW/\$]
- Relative losses [%], <2%
- Life time [Years], >10Y
- EMI – no external filters or shielded cables
- Voltage THD: better than for 3 level inverter

(B) Commercial drives:

Relative losses, <2%

- Life time 5 to 10Y
- No external filters for EMI or dv/dt
- Low grid harmonics (IEEE 519)
- Low cost

Opportunities, Grand Challenge for New Topologies

- Green drive with sinusoidal input and output
- EMI and PWM issues contained within the drive
- Utilization of parasitics to facilitate main functions
- Greater use of semiconductors on the expense of passives
- Active filtering
- Losses reduced by factor of 2
- Size and weight reduced by 2
- Same cost and life time

- The drive topologies we work on today should anticipate device performance and cost we expect in the future based on the performance trends for devices
- Focus on system level benefits

Gaps

Packaging/integration

- Packaging infrastructure for ultra high speed devices missing
 - Take benefits of parasitics
 - 3D packaging
 - Multi physics integration tools
- Life time issues for high temperature operation (thermal cycling, power cycling mostly unknown)

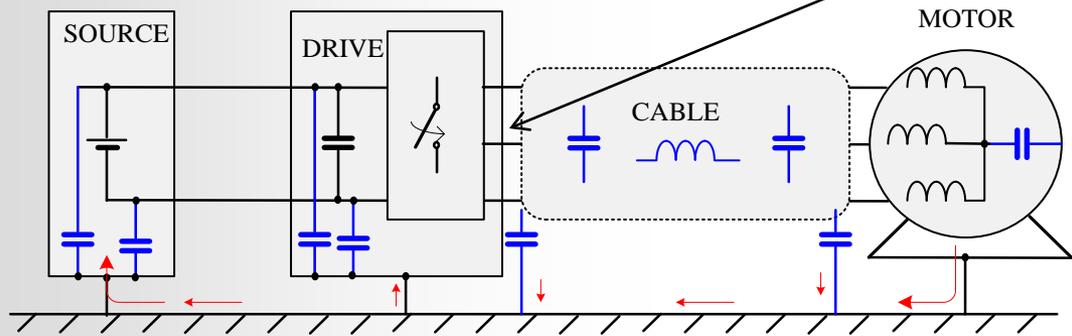
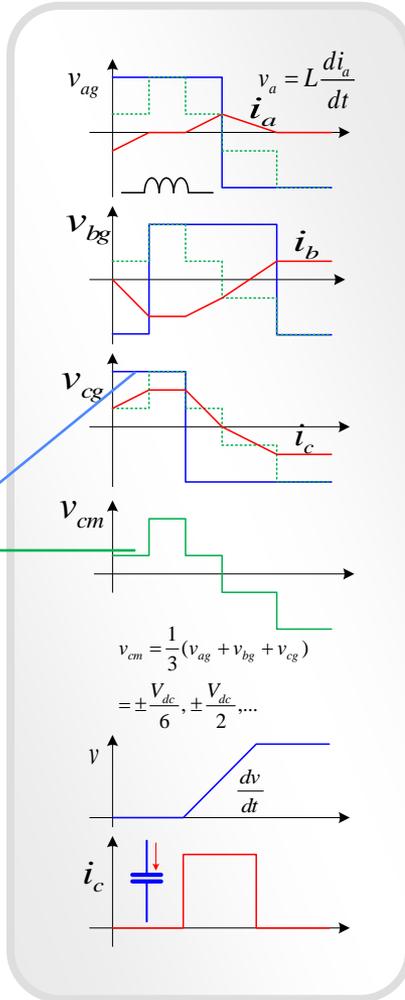
WBG device driven power converter topologies

- Low PWM frequency (1 to 20kHz)
- Highly polluted V/I output of the drive

Effects of PWM

High speed switching has negative effects on the motor and the system

- System level effects**
- EMI conductive and radiated
 - Noise in electrical circuits
- Effects on the motor**
- DM current ripple
 - Additional Cu losses
 - Additional Fe losses
 - Winding overvoltages and partial discharge
 - CM currents
 - Bearing current



Drive is a generator of voltage waveforms with sharp transitions between (high) voltage levels

Electromagnetic interference (EMI)

EMI is a **disturbance** generated by an external source that affects the operation of a sensitive electrical circuit.

EMI standards define the *regulated frequency range* and corresponding *emission limit* for products in various applications. Impact on cost.

In the context of **power electronics**, EMI is the *high frequency* voltage and current components generated by power converters

EMI: Radiated and Conducted
Conducted EMI:

- **Differential Mode (DM)**-Only flows on the power leads
- **Common Mode (CM)**-Flows to the ground.
- **CM EMI is very important for qualifications of power electronic converters**
- **PWM switching frequency, Si Devices**
 - 10 to 20kHz $P < 5kW$
 - 2 to 10kHz $5kW < P < 300kW$
 - $< 2kHz$ $P > 300kW$
- **WBG devices $f_{pwm} < 50KHz$**

Input line filter

- Increases impedance between source and drive

Mitigation for CM EMI

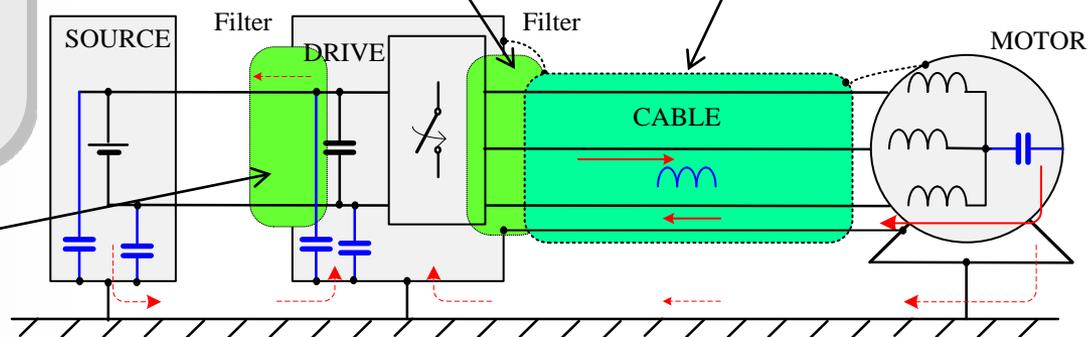
- Shielded cables/conduits between motor and drive
- EMI filters at line side of the drive
- RLC filters at the output of the drive
- Different PWM techniques to reduce CM voltage
- Active CM filter
- Good lay out of the drive
- Conductive/shielding enclosure for radiated EMI
- Integrated motor drive solutions

Output motor filter

- Softens voltage transitions
- Increases HF impedance between motor and drive

Cable

- Shielding for radiated emi
- Low impedance return path for ground currents



Over-voltages and Bearing Currents

Cause of winding isolation and bearing failures

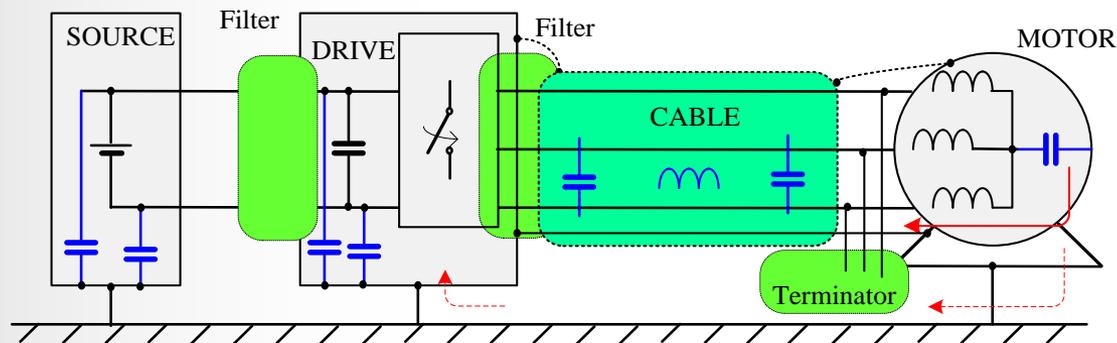
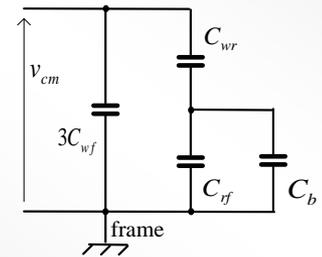
High switching speed with high dV/dt and transmission line effects/overvoltage on the motor terminals, isolation failure

- $dV/dt > 600V/\mu s$ acceptable level – bipolar technology,
- **Partial discharge** and motor winding failure, need for inverter grade wire
- For IGBT based technology start to play role for cables $> 10m$, with increased speed of semiconductor switches (x10) shorter distances $> 1m$ will start to play critical role
- Mitigation techniques:
 - Output filters (RLC) to slow voltage transition speed, preferred option for smaller power (usually simple filters like just inductor will be sufficient)
 - Motor terminator (to match impedance, close to motor winding, preferred option for larger motors)
 - Reinforced isolation on first turn on the motor winding
 - Slowdown switching devices (fpwm~5kHz)
 - Multi level inverters (reduced voltage steps)

Bearing currents

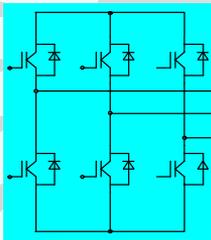
- Cause of bearings failure
- Mitigation: filters, ceramic bearings, shaft grounding, closed winding slots

High frequency equivalent circuit with main capacitances important for bearing currents

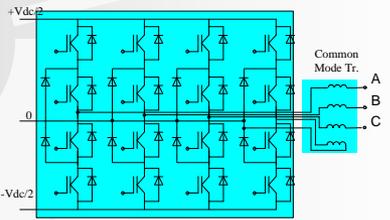


Existing drive topologies – comparison

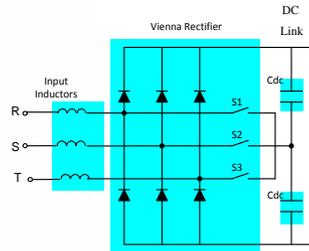
Present topologies are dominated by hard switching voltage source variants without considerations for PWM and EMI issues



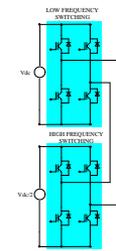
2 level



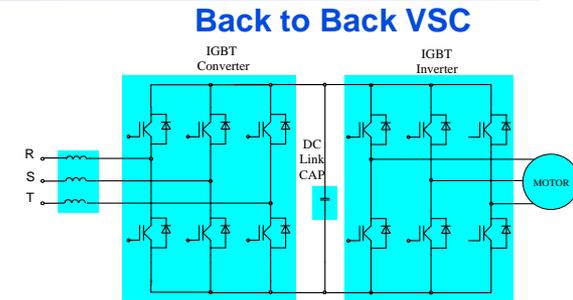
3 level 4 leg NC



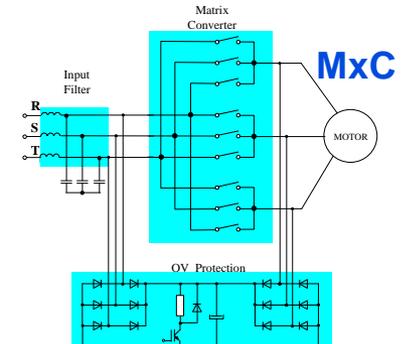
Vienna



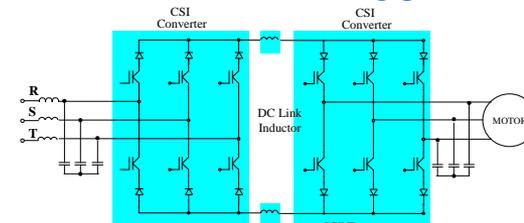
Cascaded



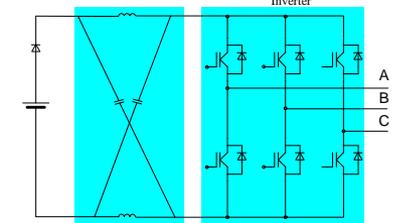
Back to Back VSC



MxC



CSI



"Z" source

	Resonant	2 Level	Multi Level	Multi level cascaded	Vienna	Back to Back VSC	CSI	Mxc	Z
Overall Complexity	Yellow	Green	Yellow	Red	Green	Green	Green	Red	Green
# of Power components	Green	Green	Green	Red	Green	Green	Yellow	Red	Green
Revers blocking devices	Yellow	Green	Green	Green	Red	Green	Red	Red	Yellow
Additional passive components to meet EMI	Yellow	Red	Yellow	Yellow	Yellow	Red	Red	Red	Red
Gate driving	Green	Green	Red	Red	Green	Green	Green	Red	Green
Power input complexity	Green	Green	Yellow	Red	Green	Green	Green	Green	Green
Control Complexity	Yellow	Green	Yellow	Yellow	Green	Green	Red	Red	Yellow
dv/dt and di/dt	Yellow	Red	Green	Yellow	Green	Red	Yellow	Red	Yellow
Conduction losses	Green	Green	Green	Green	Green	Green	Red	Green	Green
Switching losses	Green	Green	Green	Green	Green	Green	Green	Green	Green
Extra Voltage or Current stress	Red	Green	Green	Green	Green	Green	Green	Green	Yellow
THD	Yellow	Yellow	Green	Yellow	Green	Green	Green	Yellow	Green
Regeneration	Yellow	Green	Green	Red	Red	Green	Green	Yellow	Yellow

Wide Band Gap Power Devices

Devices and applications – historic perspective

Transition from BJT to IGBT technology

Fast transition

- 1988/89 IGBT lab samples available
- 1991 – Drives with IGBTs available

Packaging/integration

- Packaging infrastructure was available (all Si based)
- Life time issues (thermal cycling, power cycling mostly unknown)

Device driven power converter topologies

- Low voltage 6 step (VSI vs CSI)
- Multi level inverters
- Cascaded inverters

Transition from Si to SiC /GaN technology

Slow transition

- Cost of active/switching devices
- Need for new packaging infrastructure to support high temperature operation
- Thermal/power cycling
- High temperature passive devices and control

Packaging/integration

- Need for material and test data to guarantee long life time
- Multi physics integration tools

New power converter topologies

- Integrated filters (green drives/inverters) with sinusoidal outputs, HF – enabler)
- Broader application of multi level, cascaded and CSI inverters (enabled by low conduction losses and HF)
- Reduced size and weight, simplified cooling